

Dual Precision JFET-Input Operational Amplifier

OP215

1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die_Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/OP215

2.0 Part Number. The complete part number(s) of this specification follow:

<u>Part Number</u> <u>Description</u>

OP215-000C Dual Precision JFET-Input Operational Amplifier

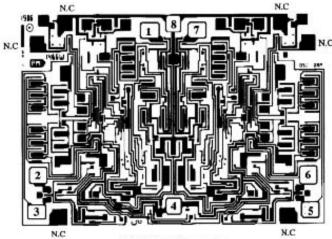
OP215R000C Radiation Tested Dual Precision JFET-Input Operational Amplifier

3.0 Die Information

3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization		
75 mil x 110 mil	19 mil ± 2 mil	Al/Cu		

3.2 Die Picture



NOTE: "N.C" - No connection.

- 1 OUTPUT A
- 2 -INPUT A
- 3 +INPUT A
- $4 V_S$
- 5 +INPUT B
- 6 -INPUT B
- 7 OUTPUT B
- $8 + V_S$

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OP215

3.3 Absolute Maximum Ratings 1/

Supply Voltage (V _S)	±22V
Differential Input Voltage	±40V
Input Voltage (V _{IN}) <u>2/</u>	±20V
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	65°C to +150°C
Junction Temperature (T _J)	+150°C
Ambient Operating Temperature	55°C to +125°C

Absolute Maximum Ratings Notes:

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- <u>2/</u> Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply.

4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Sample Size and Qual Acceptance Criteria 10/0
- (b) Qual Sample Package DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I - Dice Electrical Characteristics							
Parameter	Symbol	Symbol Conditions $\underline{1/}$		Limit Max	Units		
Input Offset Voltage	V_{IO}	$R_S = 50\Omega$		±1	mV		
Input Offset Current	I_{IO}			±50	pA		
Input Bias Current	I_{IB}			±100	pA		
Large Signal Voltage Gain	$A_{ m VO}$	$V_{OUT} = \pm 10V, R_L \ge 2k\Omega$	150		V/mV		
Output Voltage Swing	Vo	$R_L \ge 2k\Omega$	±11		V		
Supply Current	I_{S}	$V_O = 0 V$		8.5	mA		
Slew Rate	SR	$A_{VCL} = +1$, $RL \ge 2k\Omega$, $C_L = 100pF$	10		V/µs		
Common-Mode Rejection Ratio	CMRR	$V_{CM} = IVR$	86		dB		
Power Supply Rejection Ratio	PSRR	$V_S = \pm 10V$ to $\pm 16V$		51	μV/V		
Input Voltage Range	IVR		±10.2		V		

Table I Notes:

 $1/V_S = \pm 15V$, $V_{CM} = 0$ V, and $T_A = +25$ °C, unless otherwise specified.

Table II - Electrical Characteristics for Qual Samples								
Parameter	Symbol		itions <u>/</u>	Sub- groups	Limit Min	Limit Max	Units	
Input Offset Voltage	V_{IO}	$R_S = 50\Omega$		1		±1		
input Offset Voltage	V 10			2,3		±2	mV	
			M, D, L, R	1		±3		
Input Offset Current 2/	I_{IO}	$T_{\rm J} = +25^{\circ}$	°C, -55°C	1, 3		±50	pA	
input Offset Current <u>27</u>	110	$T_J = +$	125°C	2		±8	nA	
			M, D, L, R	1		±300	pA	
Input Piec Current 2/	T	$T_{\rm J} = +25^{\circ}$	°C, -55°C	1, 3		±100	pA	
Input Bias Current <u>2/</u>	I_{IB}	$T_J = +$	125°C	2		±10	nA	
			M, D, L, R	1		±6	IIA	
Larga Signal Waltaga Gain	٨	V - 10	$0V, R_L \ge 2k\Omega$	4	150		V/mV	
Large Signal Voltage Gain	A_{VO}	$\mathbf{v}_{\mathrm{OUT}} - \pm 10$		5, 6	30			
			M, D, L, R	1	10			
Output Waltage String 2/	V	$R_L \ge 2k\Omega$		4	±11		V	
Output Voltage Swing 3/	V_{O}	$R_L \ge$	10kΩ	5, 6	±12		\ \ \	
Supply Current	I_{S}	V _O =	= 0 V	1		8.5	mA	
			M, D, L, R	4		8.5		
Slew Rate <u>3</u> /	SR	$A_{VCL} = +1,$ $C_{L} =$	$R_L \ge 2k\Omega$, $100pF$	4	10		V/µs	
Common-Mode Rejection	CMRR	$V_{CM} = IVR$		1	86		dB	
Ratio <u>3</u> /	CIVIKK			2, 3	82		uБ	
Power Supply Rejection	PSRR	$V_S = \pm 10V$ to $\pm 16V$		1		51	μV/V	
Ratio <u>3</u> /	1 SIXIX			2, 3		100		
Input Voltage Range <u>3</u> /	IVR			1, 2, 3	±10.2		V	

Table II Notes:

- $1/V_S = \pm 15V$ and $V_{CM} = 0V$, unless otherwise specified.
 - $\underline{2/}\ T_A$ = -55°C for I_{IO} and I_{IB} tests, subgroup 3, is guaranteed by T_A = +25°C test.
 - <u>3/</u> Not tested post irradiation.

OP215

Table III - Life Test Endpoint and Delta Parameter (Product is tested in accordance with Table II with the following exceptions)								
Doromatar	Symbol	Sub- groups	Post Burn In Limit		Post Life Test Limit		Life	Linita
Parameter			Min	Max	Min	Max	Test Delta	Units
Input Offset Voltage	V_{IO}	1		±2		±3	±1	mV
		2, 3				±4		111 V
Input Dies Current	I_{IB}	1, 3		±175		±250	±75	pA
Input Bias Current		2				±10		nA
Input Offset Current	I_{IO}	1, 3		±87		±125		pA
		2				±8		nA

5.0 Life Test/Burn-In Information

- **5.1** HTRB is not applicable for this drawing.
- **5.2** Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- **5.3** Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	06-NOV-01
В	Add radiation limits. Update web address. Exchange file name with PM108.	9-JAN-03
С	Update 1.0 Scope Description	20-Jul-2007
D	Update header/footer and add to 1.0 Scope description.	Mar. 3, 2008
Е	Add Junction Temperature (T _J)+150°C to 3.3 Absolute Max. Ratings	April 2, 2008
F	Updated Section 4.0c note to indicate pre-screen temp testing being performed	5-JUN-2009



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